

Thyristor Module

= 2x 1200 V

49 A

 V_{τ} 1.34 V

Phase leg

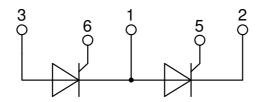
Part number

MCC44-12io8B



Backside: isolated

F1 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

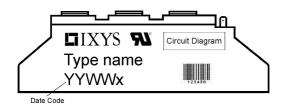
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Thyristo				"	Ratings	1	į.
Symbol	Definition	Conditions		min.	typ.	max.	Ur
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	
V _{RRM/DRM}	max. repetitive reverse/forward bl	ocking voltage	$T_{VJ} = 25^{\circ}C$			1200	
I _{R/D}	reverse current, drain current	$V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 125^{\circ}C$			5	m
V _T	forward voltage drop	I _T = 100 A	$T_{VJ} = 25^{\circ}C$			1.34	
		$I_T = 200 \text{ A}$				1.75	
		$I_{T} = 100 \text{ A}$	T _{VJ} = 125°C			1.34	
		$I_{T} = 200 \text{ A}$				1.80	
I _{TAV}	average forward current	T _C = 85°C	T _{vJ} = 125°C			49	
I _{T(RMS)}	RMS forward current	180° sine				77	
V _{T0}	threshold voltage		T _{v.i} = 125°C			0.85	
r _T	slope resistance	oss calculation only	***			3.7	m!
R _{thJC}	thermal resistance junction to cas	e				0.53	K/V
R _{thCH}	thermal resistance case to heatsi				0.20		K/V
P _{tot}	total power dissipation		T _C = 25°C		0.20	180	٧
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v.i} = 45^{\circ}C$			1.15	k
•ISM		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			1.24	k
		t = 0.0 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{VJ} = 125^{\circ}C$			980	
		t = 8.3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.06	k
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$V_R = 0 V$ $T_{VJ} = 45^{\circ}C$				
1-1	value for fusing	. , , , , , , , , , , , , , , , , , , ,	$V_{NJ} = 45 \text{ C}$ $V_{R} = 0 \text{ V}$			6.62 6.40	i .
		t = 8,3 ms; (60 Hz), sine t = 10 ms; (50 Hz), sine				4.80	!
		. , , , , , , , , , , , , , , , , , , ,	$T_{VJ} = 125$ °C				ĺ
_	iunation canacitanas	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		F.4	4.63	
C,	junction capacitance	V _R = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		54	40	р
P_{GM}	max. gate power dissipation	$t_P = 30 \mu s$	$T_{C} = 125^{\circ}C$			10	į
_		$t_{P} = 300 \mu s$				5	۷
P _{GAV}	average gate power dissipation					0.5	٧
(di/dt) _{cr}	critical rate of rise of current	**	epetitive, $I_T = 150 A$			150	A/µ
		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu s; -$					
			on-repet., $I_T = 49 A$			500	i
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125$ °C			1000	V/μ
		R _{GK} = ∞; method 1 (linear volta	ge rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	,
			$T_{VJ} = -40$ °C			1.6	,
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			100	m
			$T_{VJ} = -40$ °C			200	m
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$			0.2	,
I _{GD}	gate non-trigger current					10	m
I _L	latching current	t _p = 10 μs	$T_{VJ} = 25$ °C			450	m
	$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A}/\mu \text{s}$						į
I _H	holding current	V _D = 6 V R _{GK} = ∞	$T_{VJ} = 25$ °C			200	m
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	T _{VJ} = 25°C			2	μ
yu	- ,	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu \text{s}$				_	
t _q	turn-off time	$V_{\rm R} = 100 \text{ V}; \ I_{\rm T} = 150 \text{ A}; \ V = \frac{2}{3}$			150		μ
q		$di/dt = 10 \text{ A}/\mu \text{s} \text{ dv/dt} = 20 \text{ V}$			130		μ



Package	TO-240AA				F	Ratings	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{vJ}	virtual junction temperature				-40		125	°C
Top	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface	l etriking dietance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$	creepage distance on surface	striking distance through an	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3600			V
.002		t = 1 minute			3000			٧



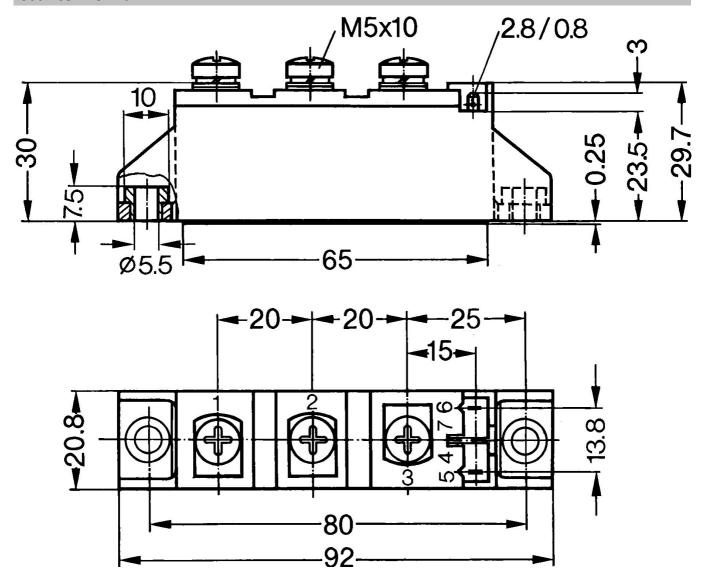
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC44-12io8B	MCC44-12io8B	Box	36	452955

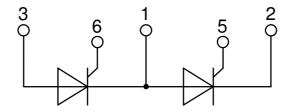
Similar Part	Package	Voltage class	
MCMA50P1200TA	TO-240AA-1B	1200	
MCMA65P1200TA	TO-240AA-1B	1200	

Equiva	alent Circuits for	Simulation	* on die level	T _{vJ} = 125 °C
$I \rightarrow V_0$)— <u>R</u> o	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$R_{0 \text{ max}}$	slope resistance *	4.1		mΩ



Outlines TO-240AA







Thyristor

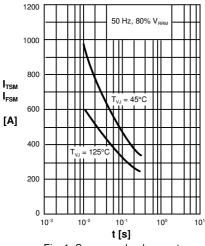


Fig. 1 Surge overload current I_{TSM} , I_{FSM} : Crest value, t: duration

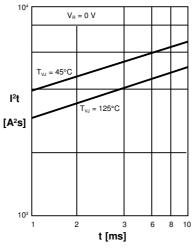


Fig. 2 I2t versus time (1-10 ms)

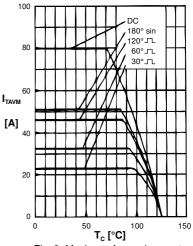


Fig. 3 Maximum forward current at case temperature

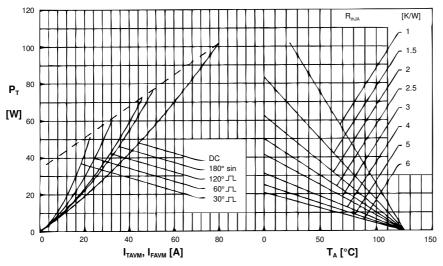


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per thyristor/diode)

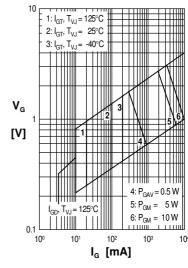


Fig. 5 Gate trigger characteristics

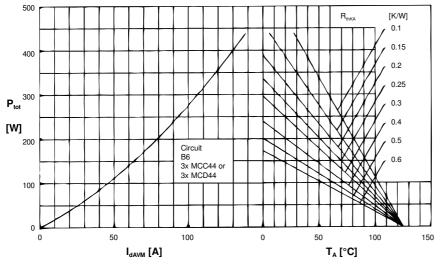


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

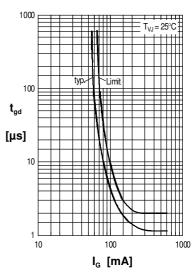


Fig. 7 Gate trigger delay time



Thyristor

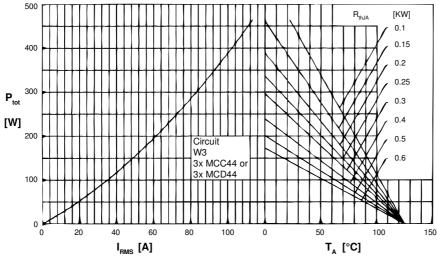


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

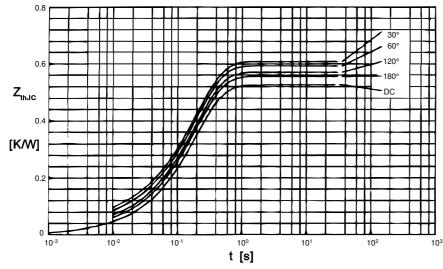


Fig. 9 Transient thermal impedance junction to case (per thyristor)

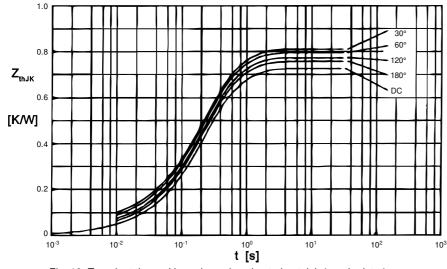


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

R_{th,IC} for various conduction angles d:

nJC		
	d	R _{thJC} [K/V
	DC	0.53
	180°	0.55
	120°	0.58
	60°	0.60
	30°	0.62

Constants for Z_{thJC} calculation:

i F	R _{thi} [K/W]	t _i [s]
1	0.015	0.0035
2	0.026	0.0200
3	0.489	0.1950

R_{thJK} for various conduction angles d:

d	R _{thJK} [K/W]
DC	0.73
180°	0.75
120°	0.78
60°	0.80
30°	0.82

Constants for Z_{thJK} calculation:

i F	R _{thi} [K/W]	t _i [s]
1	0.015	0.0035
2	0.026	0.0200
3	0.489	0.0195
4	0.200	0.6800

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